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(54) **Title**: VIAS AND CONDUCTIVE ROUTING LAYERS IN SEMICONDUCTOR SUBSTRATES

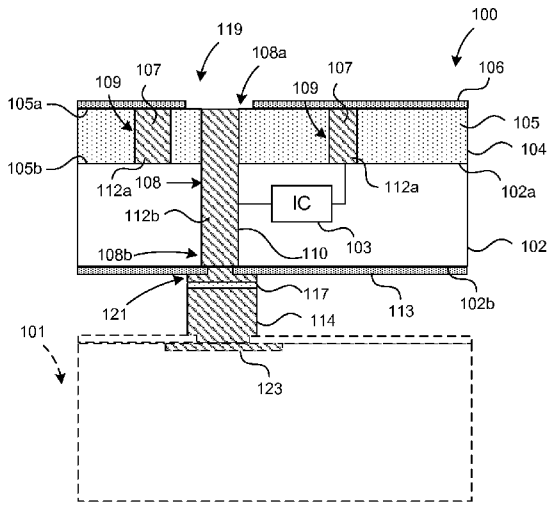


FIG. 1A

(57) **Abstract**: Through vias and conductive routing layers in semiconductor substrates and associated methods of manufacturing are disclosed herein. In one embodiment, a method for processing a semiconductor substrate includes forming an aperture in a semiconductor substrate and through a dielectric on the semiconductor substrate. The aperture has a first end open at the dielectric and a second end opposite the first end. The method can also include forming a plurality of depressions in the dielectric, and simultaneously depositing a conductive material into the aperture and at least some of the depressions.

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